PROCEEDINGS

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MULTICHAMBER AND IN-SITU PROCESSING
OF ELECTRONIC MATERIALS

Volume 1188

CONTENTS

Conference Committee v
Introduction vi

SESSION 1 **MULTICHAMBER SYSTEMS**

1188-02 **Multichamber deposition system and its application to VLSI manufacturing process**
K. Numajiri, T. Ishida, N. Takahashi, Anelva Corp. (Japan). 2

1188-04 **Multichamber and in-situ processing system design and control**
S. Chen, Univ. of North Carolina/Charlotte. 8

1188-05 **Vacuum mechatronics and inspection for self-contained manufacturing**
S. E. Belinski, M. Shirazi, Univ. of California/Santa Barbara; T. E. Seidel, SEMATECH;
S. Hackwood, Univ. of California/Santa Barbara. 21

1188-06 **Ni substrate processing using in-vacuo wafer transfer to integrate surface characterization, surface cleaning, and Ni-Cu epitaxial alloy growth**
R. P. Burns, North Carolina State Univ.; R. A. Rudder, M. J. Mantini, J. B. Posthill,
R. J. Markunas, Research Triangle Institute. 33

1188-07 **Multichamber integrated-processing UHV system for the formation of silicon heterostructures on three-inch wafers**
J. T. Fitch, J. J. Sumakeris, G. Lucovsky, North Carolina State Univ. 43

SESSION 2 **VLSI PROCESSING**

1188-08 **Process integration: the future of chipmaking (Invited Paper)**
D. N. K. Wang, Applied Materials, Inc. 56

1188-10 **Effects of multichamber processing on reliability of submicron vias**
T. Tokunaga, N. Owada, Hitachi, Ltd. (Japan). 61

1188-11 **In-situ planarization of dielectric surfaces using boron oxide**
J. Marks, K. Law, D. N. K. Wang, Applied Materials, Inc. 69

1188-12 **Characterization of a multiple-step in-situ plasma-enhanced chemical vapor deposition tetraethylorthosilicate planarization scheme for submicron manufacturing**
J. M. Perchard, H. E. Smith, R. O'Connor, Digital Equipment Corp.; J. C. Olsen, K. Law,
Applied Materials, Inc. 75

1188-13 **Cluster processing for 16-Mb DRAM production**
A. S. Bergendahl, D. V. Horak, IBM Corp. 86

1188-14 **In-situ cluster processing for advanced semiconductor technologies**
E. A. Matuszak, C. M. Hill, D. V. Horak, IBM Corp. 96

SESSION 3 **COMPOUND SEMICONDUCTOR PROCESSING**

1188-15 **Recent applications of finely focused EB/IB technologies for multichamber and in-situ processing**
H. Sawaragi, H. Kasahara, R. Mimura, M. Obata, R. Aihara, JEOL Ltd. (Japan);
W. B. Thompson, M. H. Shearer, JEOL USA, Inc. 108

1188-16 **Effects of HCl gas and hydrogen-mixture etching on in-situ cleaning of GaAs substrates in molecular beam epitaxy**
J. Saito, K. Kondo, Fujitsu Labs. Ltd., Atsugi (Japan). 115

(continued)

MULTICHAMBER AND IN-SITU PROCESSING
OF ELECTRONIC MATERIALS

Volume 1188

1188-17 **Contamination of remote plasma processes upon addition of hydrogen as a downstream reagent gas**
R. A. Rudder, S. Hattangady, J. B. Posthill, G. C. Hudson, M. J. Mantini, R. J. Markunas, Research Triangle Institute. 125

1188-18 **Electron-beam-excited GaAs maskless etching using Cl_2 nozzle installed FIB/EB combined system**
N. Takado, Y. Ide, K. Asakawa, NEC Corp. (Japan). 134

1188-09 **Formation of silicon-based heterostructures in multichamber integrated-processing thin-film deposition systems**
G. Lucovsky, S. S. Kim, D. V. Tsu, G. N. Parsons, J. T. Fitch, North Carolina State Univ. 140

SESSION 4 **IN-SITU PROCESS MONITORING**

1188-23 **AEMPES: an expert system for in-situ diagnostics and process monitoring**
S. Chen, Univ. of North Carolina/Charlotte. 152

1188-24 **In-situ spectroscopic ellipsometry investigation of ion beam damage: a kinetic study**
J. W. Andrews, Y. Z. Hu, E. A. Irene, Univ. of North Carolina/Chapel Hill. 162

1188-25 **Design of a new in-situ spectroscopic phase-modulated ellipsometer**
B. Drevillon, J. Y. Parey, M. Stchakovsky, Ecole Polytechnique (France); R. Benferhat, Y. Josserand, B. Schlayen, Instruments SA (France). 174

1188-27 **Optical emission spectroscopy for in-situ diagnostics in RIBE and RIE: velocity selective detection of particles in broad ion beams and a new method for etch rate and endpoint determination**
F. Heinrich, H. Stoll, H. Scheer, P. Hoffmann, Fraunhofer-Institut für Mikrostrukturtechnik (FRG). 185

Addendum. 195

Author Index. 196